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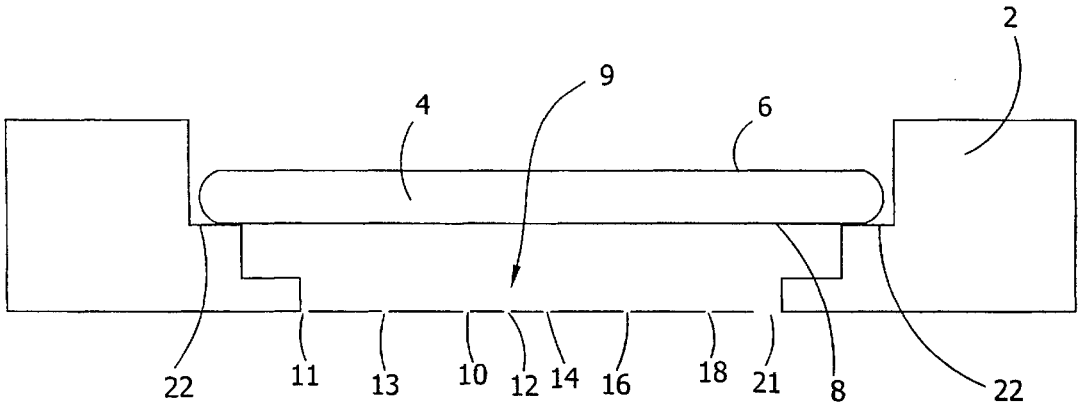
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(54) Title: MODIFIED SUSCEPTOR FOR USE IN CHEMICAL VAPOR DEPOSITION PROCESS



(57) Abstract: A modified susceptor for use in an epitaxial deposition apparatus and process is disclosed. The modified susceptor has an inner annular ledge capable of supporting a semiconductor wafer and has a plurality of holes in the surface to allow cleaning gas utilized during an epitaxial deposition process to pass through the susceptor and contact substantially the entire back surface of the semiconductor wafer and remove a native oxide layer. Also, the plurality of holes on the susceptor allows dopant atoms out-diffused from the back surface during the epitaxial deposition process to be carried away from the front surface in an inert gas stream and into the exhaust such that autodoping of the front surface is minimized.

WO 01/86034 A3